

# TMMDB3

## DIAC

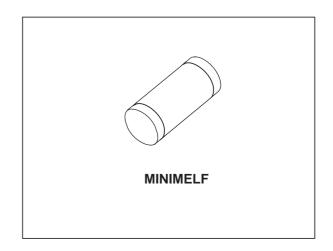
### **FEATURES**

■ V<sub>BO</sub>: 32V

■ Breakover voltage range: 28 to 36V

### **DESCRIPTION**

Functioning as a trigger diode with a fixed voltage reference, the TMMDB3 can be used in conjunction with triacs for simplified gate control circuits or as a starting element in fluorescent lamp ballasts.



## **ABSOLUTE MAXIMUM RATINGS** (limiting values)

Symbol	Parameter	Value	Unit
I <sub>TRM</sub>	Repetitive peak on-state current tp = 20 μs F= 120 Hz	2	А
Tstg Tj	Storage temperature range Operating junction temperature range	- 40 to + 125	°C

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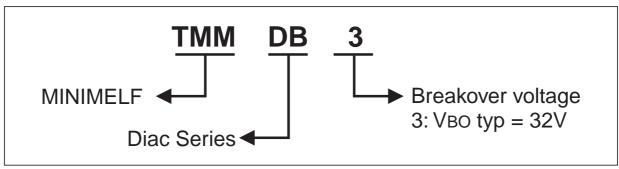
## TMMDB3

## **ELECTRICAL CHARACTERISTICS** (Tj = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions		Value	Unit
V <sub>BO</sub>	Breakover voltage *	C = 22nF **	MIN.	28	V
			TYP.	32	
			MAX.	36	
I V <sub>BO1</sub> - V <sub>BO2</sub> I	Breakover voltage symmetry	C = 22nF **	MAX.	± 3	V
ΔV	Dynamic breakover voltage *	V <sub>BO</sub> and V <sub>F</sub> at 10mA	MIN.	5	V
Vo	Output voltage *	see diagram 2 (R=20Ω)	MIN.	5	V
I <sub>BO</sub>	Breakover current *	C = 22nF **	MAX.	50	μΑ
tr	Rise time *	see diagram 3	MAX.	2	μs
I <sub>R</sub>	Leakage current *	$V_R = 0.5 V_{BO} \text{ max}$	MAX.	10	μΑ

<sup>\*</sup> Applicable to both forward and reverse directions.

### **ORDERING INFORMATION**



## OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing Mode
TMMDB3	(None)	0.04 g	2500	Tape & Reel

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<sup>\*\*</sup> Connected in parallel to the device.

Diagram 1: Voltage - current characteristic curve.

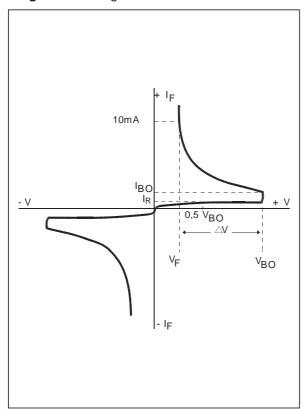


Diagram 2: Test circuit.

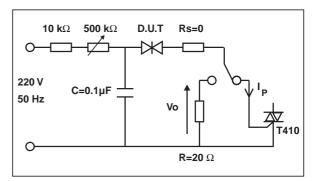
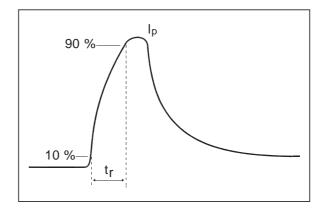
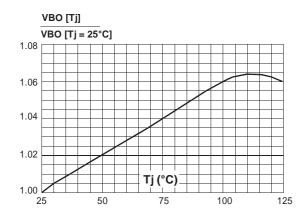


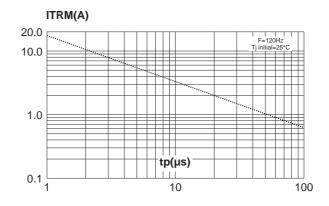
Diagram 3: Rise time measurement.



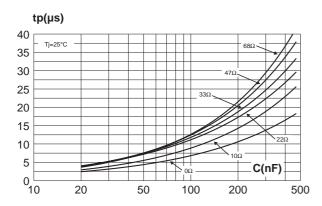
**Fig. 1:** Relative variation of VBO versus junction temperature (typical values)



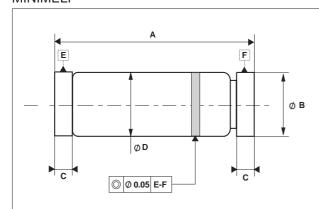
**Fig. 2:** Repetitive peak pulse current versus pulse duration (maximum values).



**Fig. 3:** Time duration while current pulse is higher 50mA versus C and Rs (typical values).

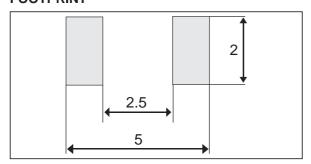


# PACKAGE MECHANICAL DATA (in millimeters) MINIMELF



REF.	DIMENSIONS					
	Millimeters				Inches	,
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	3.30	3.40	3.6	0.130	0.134	0.142
В	1.59	1.60	1.62	0.063	0.063	0.064
С	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

#### **FOOTPRINT**



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